L Number	Hits	Search Text	DB	Time stamp
1	250577	MOSFET CMOS MOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 17:57
2	439	strained with channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 17:57
3	185	(MOSFET CMOS MOS) same (strained with channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 17:58
4	27	(strained with channel) same (insulat$3 with (oxide dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 17:58